

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
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ATTY DOCKET NO.

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SERIAL NO.

New Continuation of

10/188,744

10/773,217

APPLICANT

Yasuo OHBA

FILING DATE

Herein

2-9-04

GROUP

2822

LIST OF REFERENCES CITED BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
IMS	AA	4,792,958	12/20/88	OHBA, et al.	372	45.01	
	AB	4,809,287	02/28/89	OHBA, et al.	372	45.01	
	AC	4,835,117	05/30/89	OHBA, et al.	438	40	
	AD	4,949,349	08/14/90	OHBA, et al.	372	45.01	
	AE	4,910,743	03/20/90	OHBA, et al.	372	45.01	
	AF	4,928,285	05/22/90	KUSHIBE, et al.	372	45.01	
	AG	4,893,313	01/09/90	HATAKOSHI, et al.	372	46.01	
	AH	5,076,800	12/31/91	MILNES, et al.	439	394	
	AI	5,036,521	07/30/91	HATAKOSHI, et al.	372	45.01	
	AJ	5,168,077	12/01/92	ASHIZAWA, et al.	117	102	
	AK	5,042,043	08/20/91	HATANO, et al.	372	45.02	
	AL	5,005,057	04/02/91	IZUMIYA, et al.	257	13	
	AM	5,079,184	01/07/92	HATANO, et al.	117	102	
IMS	AN	5,103,271	04/07/92	IZUMIYA, et al.	257	94	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
IMS	AO	2000-31588	01/28/00	JAPAN		X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

IMS	AW	Y. OHBA, et al., Japanese Journal of Applied Physics, Vol. 37 Part 2, No. 8A, pp. L 905 - L 906, "FABRICATION AND CHARACTERIZATION OF AlGaIn/GaN DOUBLE-HETEROLASER STRUCTURES ON SAPPHIRE SUBSTRATES USING SINGLE CRYSTALLINE AlN BUFFER LAYERS," August 1, 1998.
	AX	
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

J. M. Szwed

Date Considered

12-11-06

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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